

ABSTRACT OF THE DISCLOSURE

In a semiconductor device, pinning regions 105 are disposed along the junction portion of a drain region 102 and a channel forming region 106 locally in a channel width direction. With this structure, because the spread of a depletion layer from a drain side is restrained by the pinning regions 105, a short-channel effect can be restrained effectively. Also, because a passage through which carriers move is ensured, high mobility can be maintained.